

CMS120N080W

SiC N-Channel 1200-V (D-S) MOSFET

Features

- High speed switching
- High blocking voltage
- Fast reverse recovery

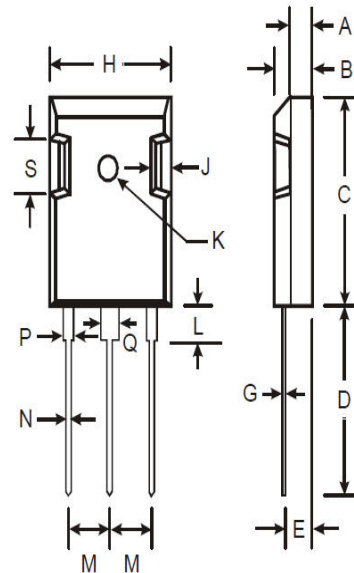
Benefits

- Low capacitance
- High system efficiency
- Easy to parallel Applications

Typical Applications

- Solar inverters
- Switch mode power supplies, UPS
- Induction heating and welding
- EV charging stations
- High voltage DC/DC converters
- Motor drive

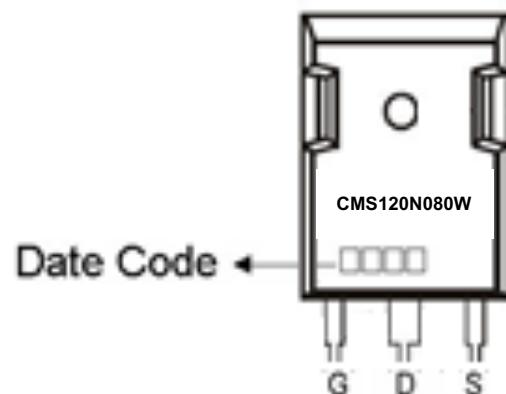
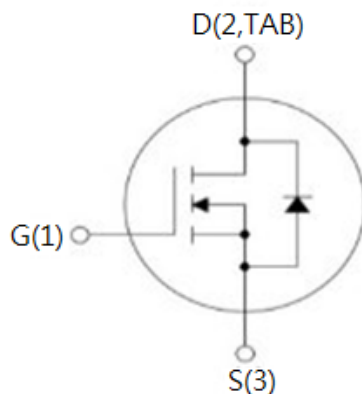
Package Dimension



TO247		
Dim	Min	Max
A	1.9	2.1
B	4.85	5.15
C	20.3	21.75
D	19.60	20.1
E	2.2	2.6
G	0.51	0.76
H	15.45	16.25
J	1.93	2.18
K	2.9Ø	3.2Ø
L	3.78	4.38
M	5.2	5.7
N	1.0	1.4
P	1.8	2.2
Q	2.8	3.2
S	4.4 Typ	
All Dimensions in mm		

Marking

Package type : TO-247



RoHS Compliant

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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{DS}	Drain-Source Voltage	1200	V
V_{GS}	Gate-Source Voltage	-5/20	V
I_D	Continuous Drain Current ($T_C = 25^\circ\text{C}$)	34	A
	Continuous Drain Current ($T_C = 100^\circ\text{C}$)	25	A
$I_{D,pulse}$	Pulsed Drain Current	80	A
P_{tot}	Power Dissipation ($T_C = 25^\circ\text{C}$)	188	W
E_{AS}	Single Pulse Avalanche Energy, $I_{AS}=20\text{A}$, $V=50\text{V}$, $L=1\text{mH}$	200	mJ
T_J/T_{STG}	Operating Junction and Storage Temperature	-55...175	$^\circ\text{C}$

Thermal Resistance Ratings

Symbol	Parameter	Maximum	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient	40	$^\circ\text{C/W}$
$R_{\theta JC}$	Maximum Junction-to-Case	0.8	$^\circ\text{C/W}$

Static Electrical Characteristics, ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=10\text{mA}$	2.0	2.8	4.0	V
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=1\text{mA}$	1200	-	-	V
I_{GSS+}	Gate-Source Leakage Current	$V_{DS}=0\text{V}$, $V_{GS}=20\text{V}$	-	0.1	100	nA
I_{GSS-}		$V_{DS}=0\text{V}$, $V_{GS}=-5\text{V}$	-	-	-100	
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=1200\text{V}$, $V_{GS}=0\text{V}$	-	-	1.0	μA
		$V_{DS}=1200\text{V}$, $V_{GS}=0\text{V}$, $T_J=175^\circ\text{C}$	-	1.0	-	
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS}=20\text{V}$, $I_D=20\text{A}$	-	77	100	m Ω
		$V_{GS}=20\text{V}$, $I_D=10\text{A}$	-	71	90	
		$V_{GS}=20\text{V}$, $I_D=20\text{A}$, $T_J=125^\circ\text{C}$	-	106	-	
		$V_{GS}=20\text{V}$, $I_D=20\text{A}$, $T_J=175^\circ\text{C}$	-	134	-	
R_g	Gate Input Resistance	$f=1\text{MHz}$, $V_{AC}=25\text{mV}$, D-S short	-	3.0	-	Ω

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AC Electrical Characteristics, ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Q_g	Total Gate Charge	$V_{DD}=800\text{ V}$, $I_{DS}=20\text{ A}$, $V_{GS}=-5/20\text{ V}$	-	58	-	nC
Q_{gs}	Gate-Source Charge		-	19	-	
Q_{gd}	Gate-Drain ("Miller") Charge		-	18	-	
$t_{d(on)}$	Turn-On Delay Time	$V_{DD}=800\text{ V}$, $I_{DS}=20\text{ A}$, $R_{G(ext)}=2.5\ \Omega$, $V_{GS}=-5/+20\text{ V}$, $L=975\ \mu\text{H}$	-	10	-	ns
t_r	Rise Time		-	6	-	
$t_{d(off)}$	Turn-Off Delay Time		-	16	-	
t_f	Fall Time		-	10	-	
C_{ISS}	Input Capacitance	$V_{GS}=0\text{ V}$, $V_{DS}=1000\text{ V}$, $f=200\text{ kHz}$, $V_{AC}=25\text{ mV}$	-	1377	-	pF
C_{OSS}	Output Capacitance		-	62	-	
C_{RSS}	Reverse Transfer Capacitance		-	4	-	
E_{OSS}	Coss Stored Energy		-	38	-	
E_{on}	Turn-On Switching Energy	$V_{DD}=800\text{ V}$, $I_{DS}=20\text{ A}$, $R_{G(ext)}=2.5\ \Omega$, $V_{GS}=-5/+20\text{ V}$, $L=975\ \mu\text{H}$	-	410	-	μJ
E_{off}	Turn-Off Switching Energy		-	22	-	
E_{tot}	Total Switching Energy		-	432	-	
Q_g	Total Gate Charge	$V_{DD}=800\text{ V}$, $I_{DS}=20\text{ A}$, $V_{GS}=-5/20\text{ V}$	-	58	-	nC
Q_{gs}	Gate to Source Charge		-	18	-	
Q_{gd}	Gate to Drain Charge		-	17	-	

Body Diode Characteristics, ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_S	Max Continuous Diode Forward Current	$V_{GS}=-5\text{ V}$, $T_C=25^{\circ}\text{C}$	-	-	43	A
V_{SD}	Diode Forward Voltage	$V_{GS}=-5\text{ V}$, $I_S=10\text{ A}$	-	3.8	-	V
t_{rr}	Reverse Recovery Time	$I_S=20\text{ A}$, $V_R=800\text{ V}$, $V_{GS}=-5\text{ V}$, $di/dt=3500\text{ A}/\mu\text{s}$	-	26	-	ns
Q_{rr}	Reverse Recovery Charge		-	124	-	nC
I_{rrm}	Peak Reverse Recovery Current		-	8	-	A

- Typical Electrical Characteristics

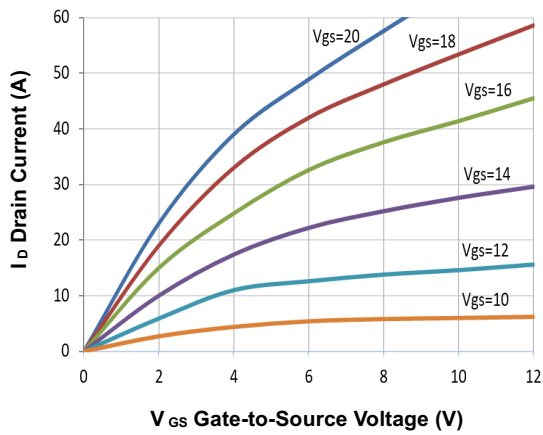


FIG.1-Output Characteristics $T_J = -55^\circ\text{C}$

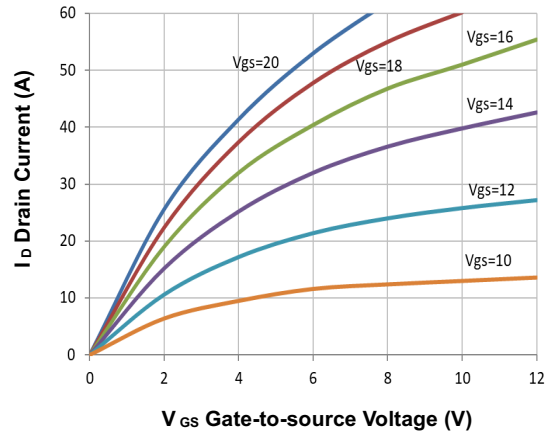


FIG.2- Output Characteristics $T_J = 25^\circ\text{C}$

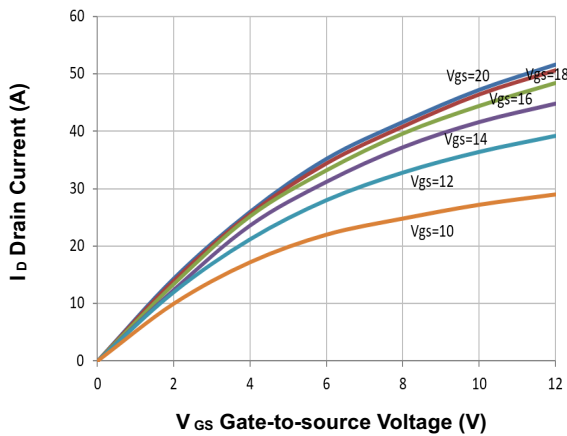


FIG.3- Output Characteristics $T_J = 175^\circ\text{C}$

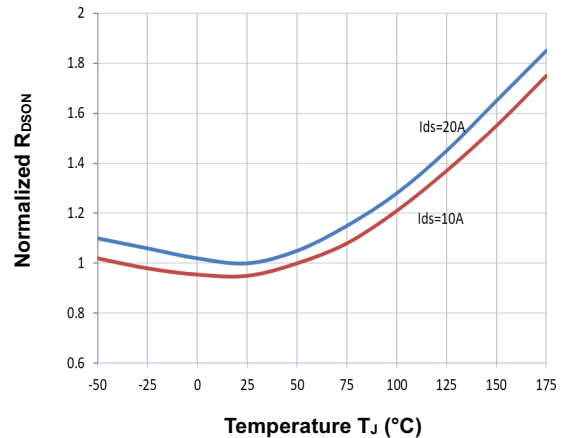


FIG.4-Normalized $R_{DS(on)}$ vs. Temperature T_J

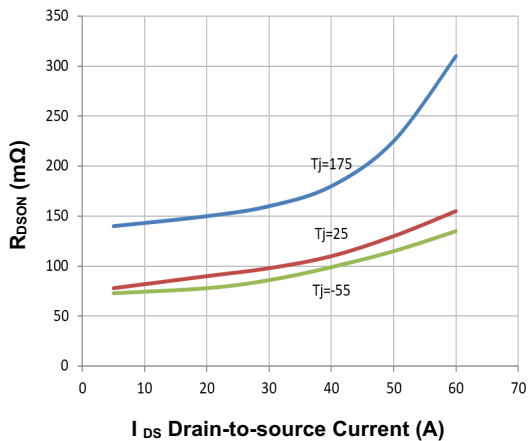


FIG.5- On-Resistance vs. Drain Current For Various Temperature

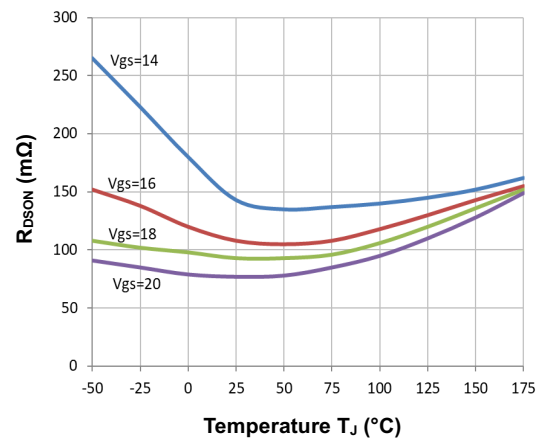


FIG.6- On-Resistance vs. Temperature For Various Gate Voltages

- Typical Electrical Characteristics

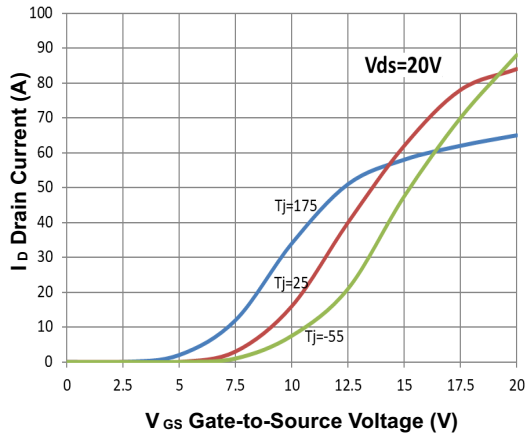


FIG.7-Transfer Characteristic for Various Junction Temperatures

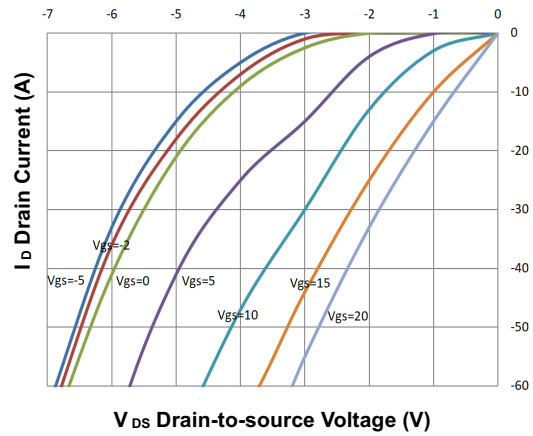


FIG.8- Body Diode Characteristics at $T_J=-55^\circ C$

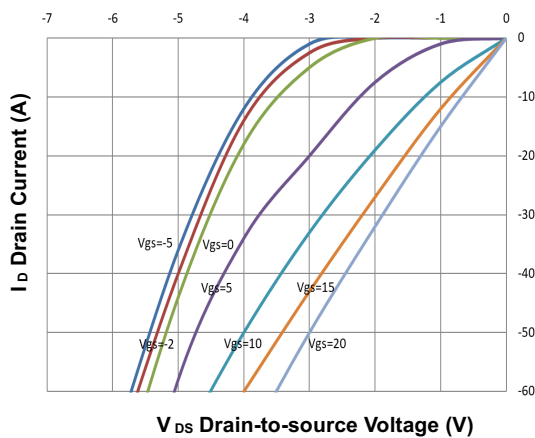


FIG.9- Body Diode Characteristics at $T_J=25^\circ C$

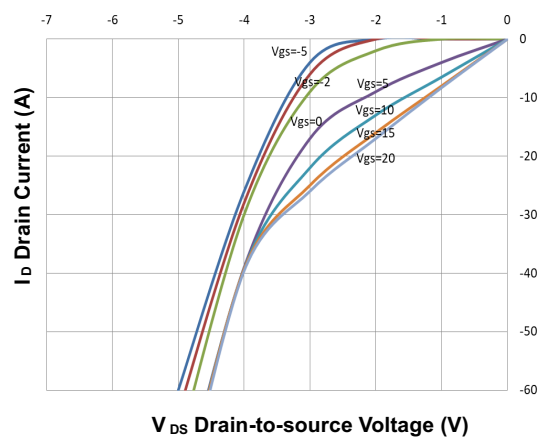


FIG.10- Body Diode Characteristics at $T_J=175^\circ C$

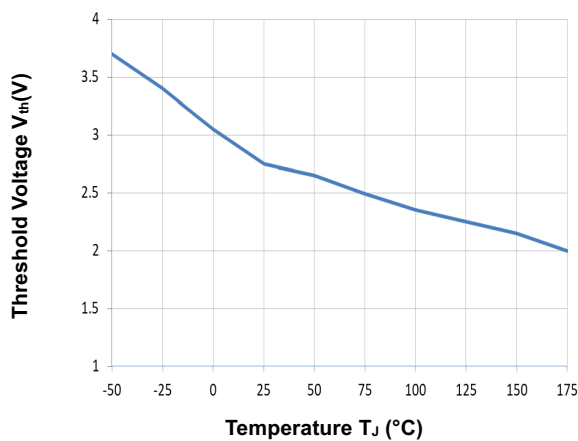


FIG.11-Threshold Voltage vs. Temperature

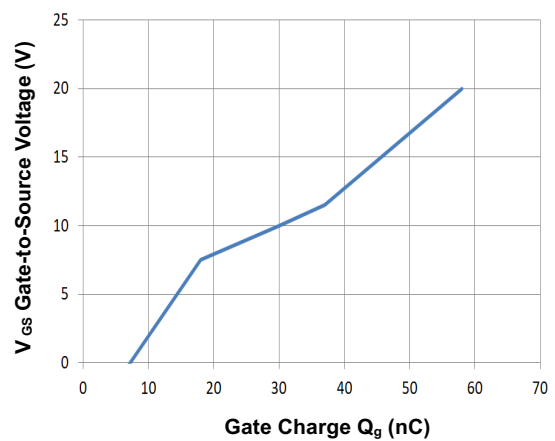


FIG.12- Gate Charge Characteristics

- Typical Electrical Characteristics

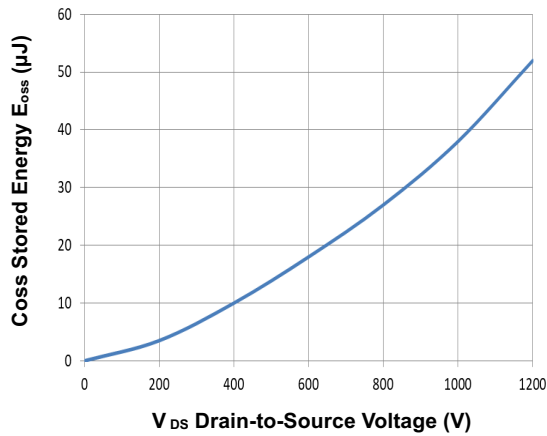


FIG.13- Output Capacitor Stored Energy

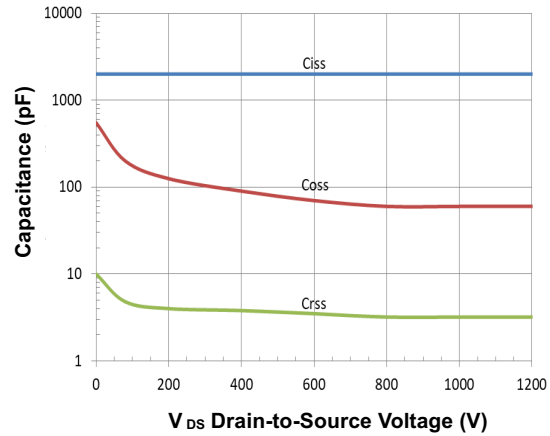


FIG.14- Capacitance vs Drain-Source Voltage

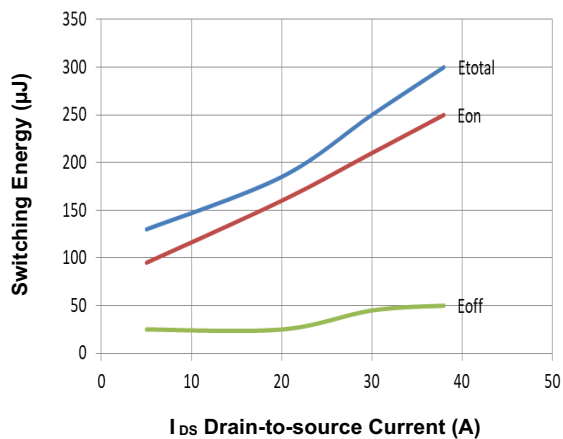


FIG.15- Clamped Inductive Switching Energy vs. Drain Current

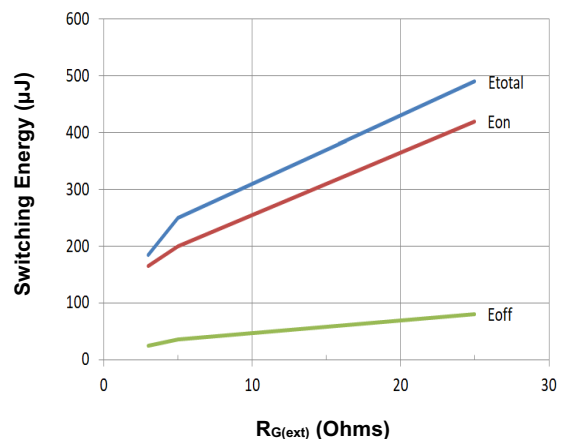


FIG.16- Clamped Inductive Switching Energy vs. $R_{G(ext)}$

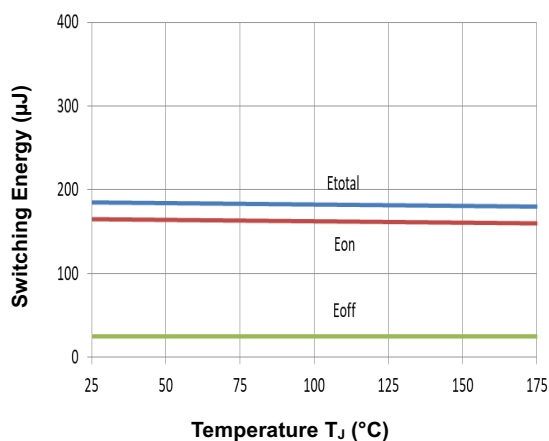


FIG.17-Clamped Inductive Switching Energy vs. Temperature

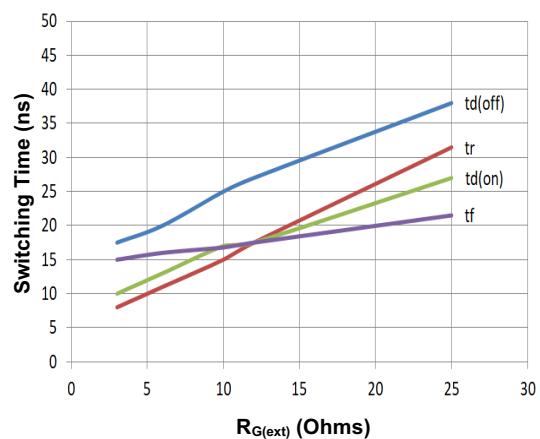


FIG.18- Switching Times vs $R_{G(ext)}$

- Typical Electrical Characteristics

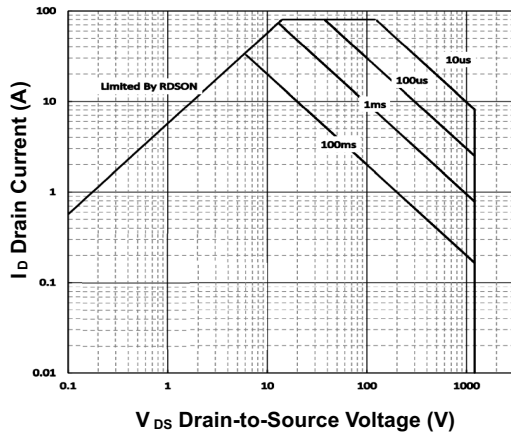


FIG.19- Safe Operating Area

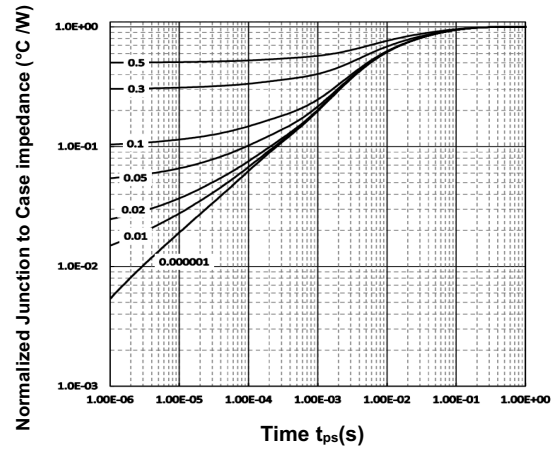


FIG.20- Transient Thermal impedance (Junction to Case)

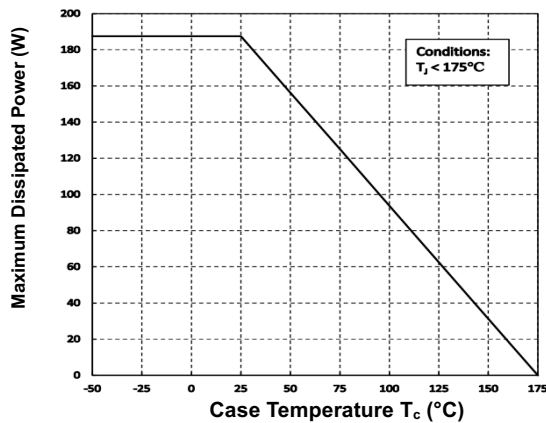


FIG.21- Maximum Power Dissipation Derating vs Case Temperature

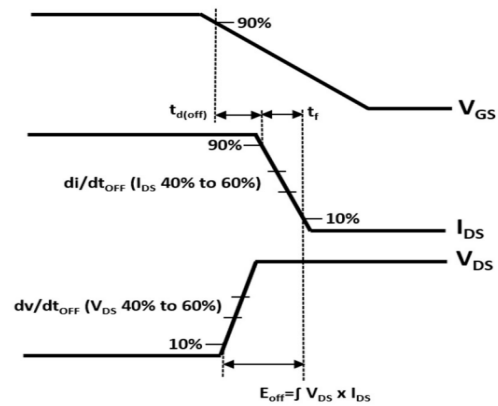


FIG.22- Turn-off Transient Definitions

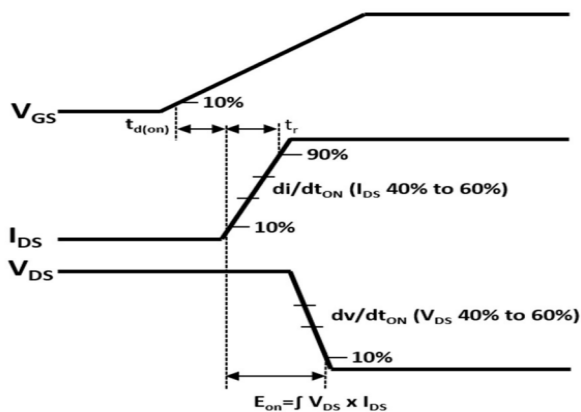


FIG.23-Turn-on Transient Definitions

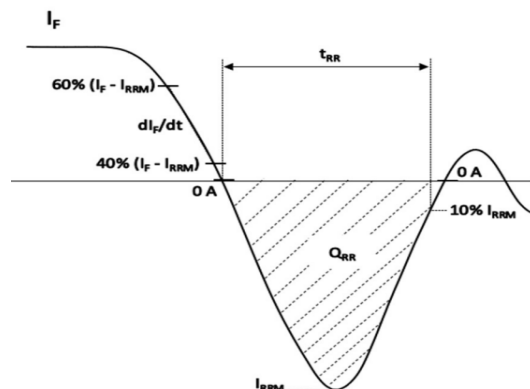


FIG.24- Reverse Recovery Definitions

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